

NPN General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1.5 A. Sourced from Process 37.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	2.0	А
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	м	Max	
		TN6714A	*NZT6714	
P _D	Total Device Dissipation	1.0	1.0	W
	Derate above 25°C	8.0	8.0	mW/∘C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	50		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	125	°C/W

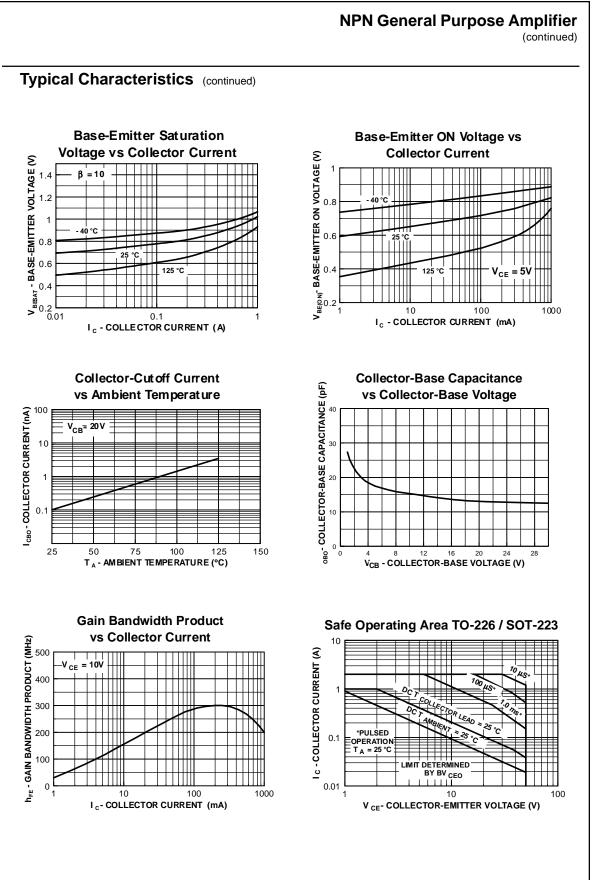
*Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

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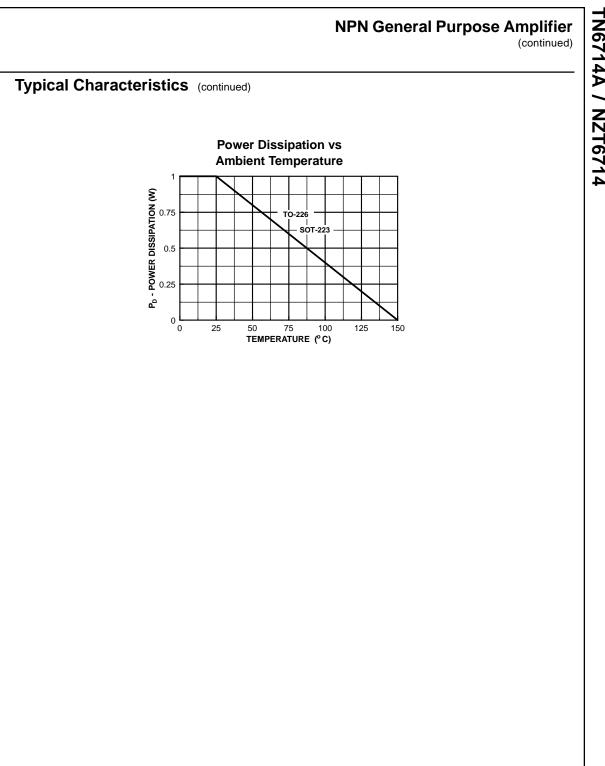
NPN General Purpose Amplifier

	Parameter	Test Conditions	Min	Max	Units
OFF CHAP	RACTERISTICS				
(BR)CEO	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0$	30		V
(BR)CBO	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	40		V
(BR)EBO	Emitter-Base Breakdown Voltage	$I_{\rm E} = 100 \ \mu {\rm A}, \ I_{\rm C} = 0$	5.0		V
во	Collector-Cutoff Current	$V_{CB} = 40 \text{ V}, I_E = 0$		0.1	μA
BO	Emitter-Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_C = 0$		0.1	μA
)N CHAR	ACTERISTICS				
FE	DC Current Gain	I _C = 10 mA, V _{CE} = 1.0 V	55		
		$I_{C} = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$	60	0.75	
	Collector-Emitter Saturation Voltage	$I_{\rm C} = 1.0$ A, $V_{\rm CE} = 1.0$ V $I_{\rm C} = 1.0$ A, $I_{\rm B} = 100$ mA	50	250 0.5	V
CE(sat)	Base-Emitter On Voltage	$I_{\rm C} = 1.0 \text{ A}, I_{\rm B} = 100 \text{ mA}$		1.2	V
MALL SI	GNAL CHARACTERISTICS Small-Signal Current Gain	$I_{c} = 50 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 20 MHz	2.5	25	
cb	Collector-Base Capacitance	$V_{CB} = 10 \text{ mA}, I_E = 0, f = 1.0 \text{ MHz}$		30	pF
Typica	al Characteristics				
1	al Characteristics Typical Pulsed Current Gain vs Collector Current	Collector-E ᢓ Voltage vs 0			
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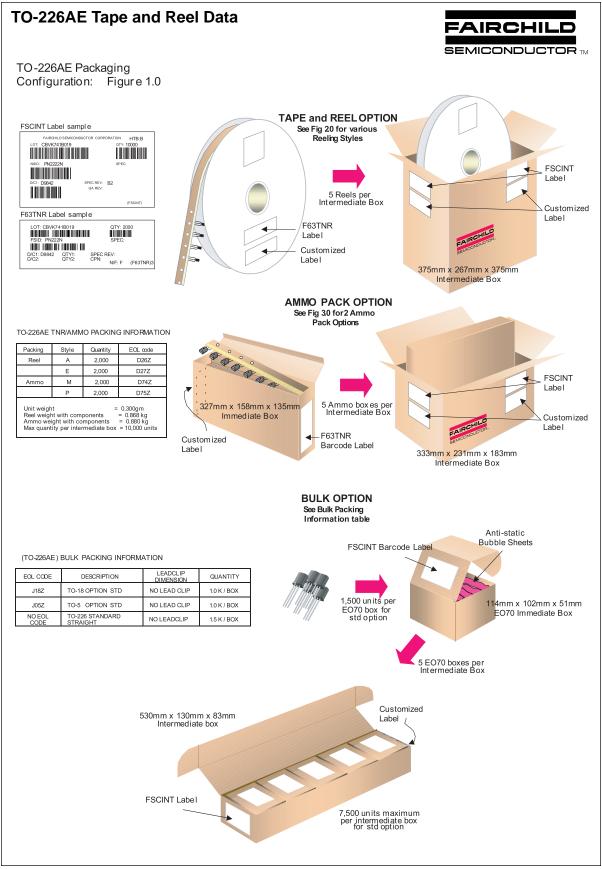
TN6714A / NZT6714

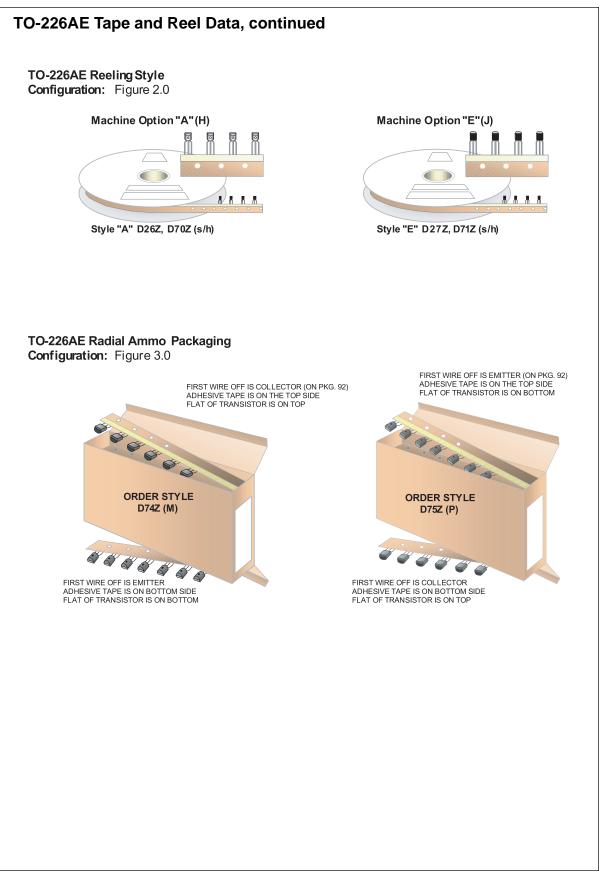


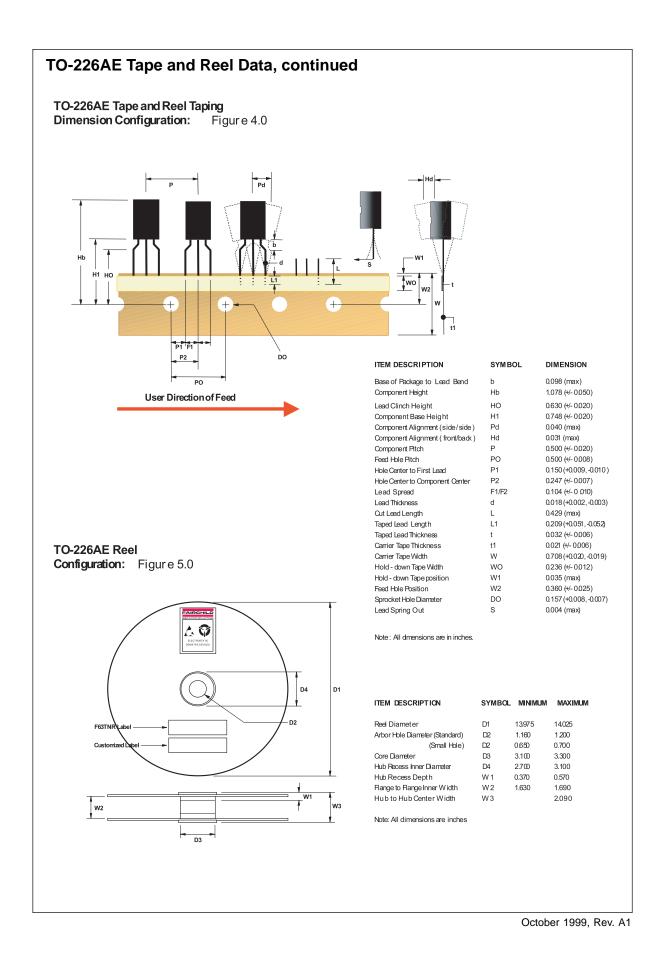
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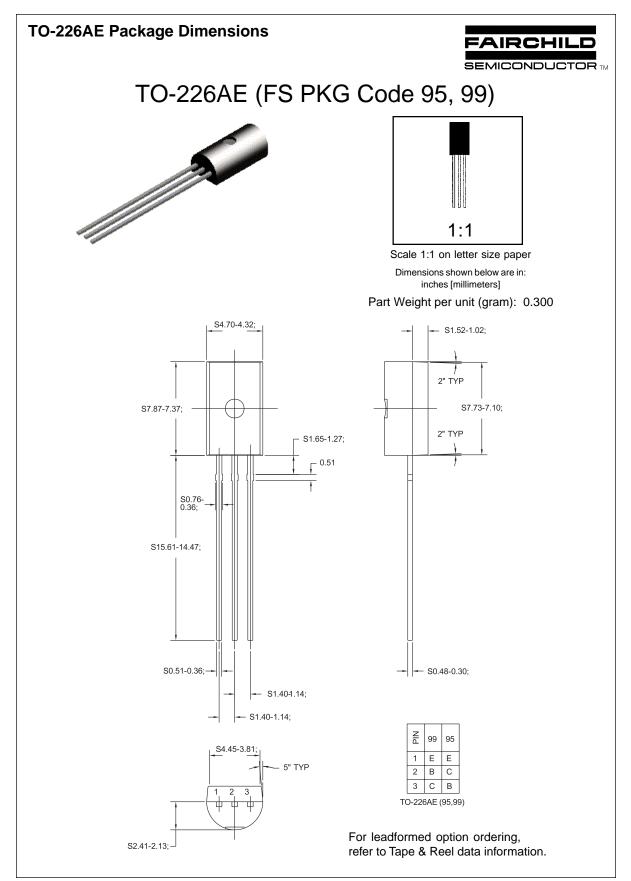


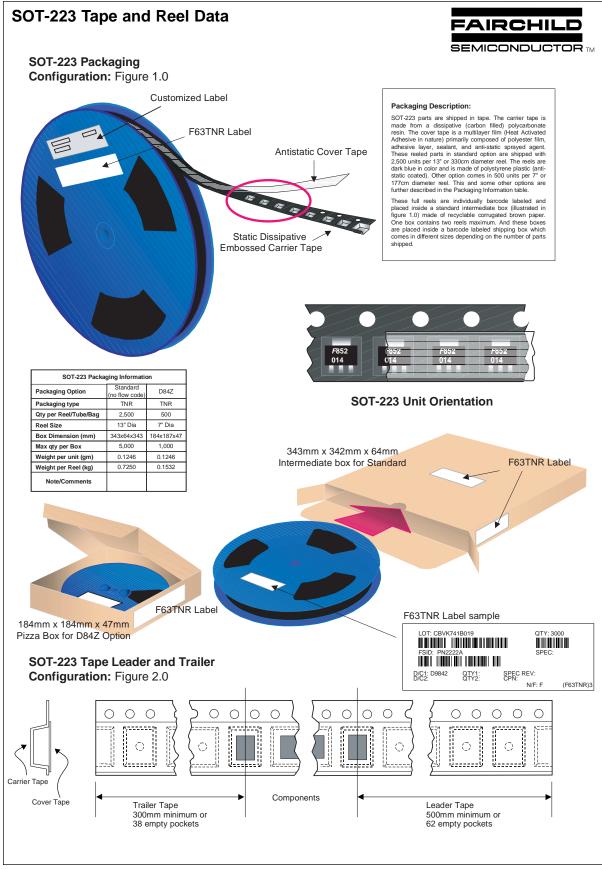
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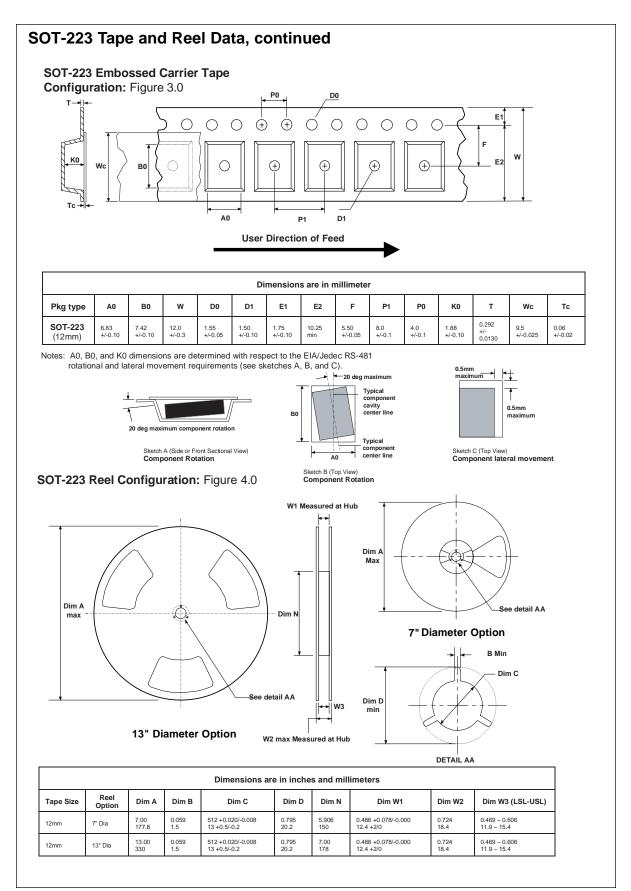


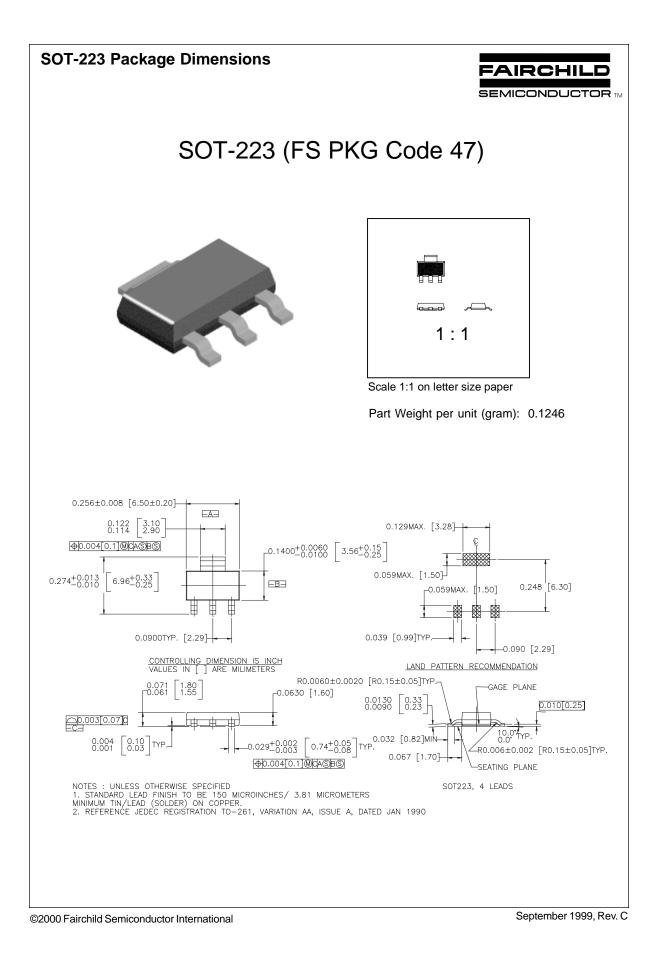




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